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Serial No. 10/690,200

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-5. (Canceled)

6. (Currently Amended) A method of making a transistor on a substrate having a dielectric layer thereon comprising:
forming a gate structure overlying the dielectric layer, the dielectric layer including gate structure having a gate oxide layer ~~formed on the dielectric layer~~, a polysilicon layer formed on the gate oxide layer and a metal silicide layer formed on the polysilicon layer and a dielectric cap formed on the metal silicide layer, ~~the gate structure having~~ a first sidewall and a second sidewall[[,]] defining a first contact region, a second contact region and a channel region therebetween; and
forming first, second and third subregions within the contact regions, each subregion having a dopant concentration that is different from that of the other two subregions, wherein forming said subregions comprises:
introducing a first dopant into the substrate to form a first subregion, the first subregion being generally aligned with the sidewalls of the gate structure;
forming a first single thin layer sidewall spacer of dielectric material overlying the sidewalls, the first single thin layer sidewall spacer formed by depositing a thin conformal layer of dielectric material over the substrate and etching to a predetermined thickness over the sidewalls;
providing an annealing/oxidation step at an elevated temperature;
forming a second single layer sidewall spacer overlying the first single thin layer spacer, the second single layer sidewall spacer having a thickness greater than the first single thin layer sidewall spacer;
introducing a second dopant into the substrate to form the second subregion, the second subregion being generally aligned with the second single layer sidewall spacer;